

Fabrication and characterization of graphene oxide and reduced graphene oxide on MoS_2 film for IR detectors

Anurag Gartia¹, Prof. Jyoti Prakash Kar¹



¹Department of Physics and Astronomy, National Institute of Technology Rourkela

ABSTRACT

In recent years, infrared detectors have been widely used in surveillance, medical diagnosis, remote sensing devices, defence, industrial automation, communication, astronomy, where the advance materials are required to enhance the device performance. Graphene has gained tremendous attention in the field of photonics and electronics because of its numerous outstanding properties like zero bandgap, exceptionally high crystal and electronic quality, high mechanical strength, and electrical conductivity. In the cutting edge of technology, the graphene oxide - molybdenum disulphide hybrid structures have drawn tremendous attention for the development of high efficiency IR detectors, where MoS₂ film is used for generation of photoelectrons, and graphene oxide is used to enhance the carrier mobility. In this work, modified Hummer's method is used for the fabrication of graphene oxide (GO), where reduced graphene oxide (rGO) is obtained by the thermal reduction of GO at 350 °C for 1 hour. The appearance of XRD peak, corresponding to (001) and (002) peaks for GO and rGO, respectively confirms the crystalline nature of the materials. The characteristic Raman peaks of GO and rGO are observed at 1358 cm⁻¹ and 1597 cm⁻¹, which correspond to the D bands and G bands, respectively. The layered structure of rGO is observed by Scanning electron microscope (SEM) technique. On the other hand, MoS₂ film was grown by the sulphonation of sputtered Mo film on silicon substrate (p-type, 1-10 Ω .cm, 525 ± 20 µm). The characteristics XRD peak of MoS₂, thin film. The. Post-deposition morphological and electrical properties of reduced graphene oxide and MoS₂ thin film is carried out and co-related for next generation optoelectronic devices.

Keywords: rGO, Hummer's method, MoS₂, XRD, Raman



	GO powder	EDX analysis of GO powder
$\begin{array}{c} \begin{array}{c} & & & \\ & & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & & \\ & & \\ & & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & & $	aman peaks at aman peaks at $358 ext{ cm}^{-1}$ orresponding to bands and $597 ext{ cm}^{-1}$ orresponding to be G bands, espectively.	 ✓ Graphene oxide and reduced graphene oxide are prepared by modified Hummer's method. ✓ A dominant diffraction peak (0 0 1) of GO is positioned at 20 = 9.96°. In case of rGO powder, broad peaks centered at around 25.25° for (0 0 2) plane and around 43° for (1 0 1) plane are obtained. ✓ Raman spectra of both GO and rGO powder show prominent Raman peaks at 1358 cm⁻¹ corresponding to the D bands and 1597 cm⁻¹ corresponding to the G bands, respectively. ✓ EDX spectra of GO powder confirms the atomic percentage of carbon and oxygen 55.41% and 44.59% respectively. ✓ EDX spectra of rGO powder confirms the atomic percentage of carbon and oxygen 79.53% and 20.47% respectively, which confirms the reduction of oxygen and increase of carbon to oxygen ratio.
Raman spectrum of (a) GO and (b) rGO powder		REFERENCS
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